# FFSP2065B-F085

# **Silicon Carbide Schottky Diode**

# 650 V, 20 A

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 94 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Applications**

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

## **ABSOLUTE MAXIMUM RATINGS**

(T<sub>C</sub> = 25°C, Unless otherwise specified)

| Symbol                            | Parar  | FF-<br>SP2065B-F085                         | Unit |    |  |
|-----------------------------------|--|---|------|----|--|
| $V_{RRM}$                         | Peak Repetitive Rev                              | 650   | ٧    |    |  |
| E <sub>AS</sub>                   | Single Pulse Avalan                              | che Energy (Note 1)                         | 94   | mJ |  |
| lF                                | Continuous Rectified<br>@ T <sub>C</sub> < 141°C | 20  | Α    |    |  |
|                                   | Continuous Rectified<br>@ T <sub>C</sub> < 135°C | 22.5  |      |    |  |
| I <sub>F, Max</sub>               | Non-Repetitive<br>Peak Forward                   | T <sub>C</sub> = 25°C, 10 μs                | 882  | Α  |  |
|                                   | Surge Current                                    | T <sub>C</sub> = 150°C, 10 μs               | 798  |    |  |
| I <sub>F, SM</sub>                | Non-Repetitive<br>Forward<br>Surge Current       | Half-Sine Pulse,<br>t <sub>p</sub> = 8.3 ms | 84   | Α  |  |
| P <sub>tot</sub>                  | Power Dissipation                                | T <sub>C</sub> = 25°C                       | 150  | W  |  |
|                                   |  | T <sub>C</sub> = 150°C                      | 25   |    |  |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storag<br>Range                    | -55 to +175                                 | °C   |    |  |

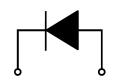
<sup>1.</sup>  $E_{AS}$  of 94 mJ is based on starting  $T_J = 25^{\circ}C$ , L = 0.5 mH,  $I_{AS} = 19.4$  A, V = 50 V.



## ON Semiconductor®

www.onsemi.com

#### **ELECTRICAL CONNECTION**



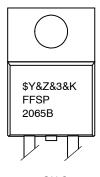
1. Cathode

2. Anode



TO-220-2LD CASE 340BB

#### **MARKING DIAGRAM**



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Numeric Date Code

&K = Lot Code

FFSP2065B-F085 = Specific Device Code

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# FFSP2065B-F085

## THERMAL CHARACTERISTICS

| Symbol         | Parameter                                  | Ratings | Unit |
|----------------|--|---------|------|
| $R_{	heta JC}$ | Thermal Resistance, Junction to Case, Max. | 1.0     | °C/W |

# PACKAGE MARKING AND ORDERING INFORMATION

| Part Number    | Top Mark  | Package | Packing Method | Reel Size | Tape Width | Quantity |
|----------------|-----------|---------|----------------|-----------|------------|----------|
| FFSP2065B-F085 | FFSP2065B | TO220   | Tube           | N/A       | N/A        | 50 Units |

# **ELECTRICAL CHARACTERISTICS** $T_C = 25^{\circ}C$ unless otherwise noted

| Symbol         | Parameter               | Test Conditions                                | Min. | Тур. | Max. | Unit |
|----------------|-------------------------|--|------|------|------|------|
| V <sub>F</sub> | Forward Voltage         | I <sub>F</sub> = 20 A, T <sub>C</sub> = 25°C   | -    | 1.38 | 1.7  | V    |
|                |                         | I <sub>F</sub> = 20 A, T <sub>C</sub> = 125°C  | -    | 1.6  | 2.0  |      |
|                |                         | I <sub>F</sub> = 20 A, T <sub>C</sub> = 175°C  | -    | 1.72 | 2.4  |      |
| I <sub>R</sub> | Reverse Current         | V <sub>R</sub> = 650 V, T <sub>C</sub> = 25°C  | -    | 0.5  | 40   | μΑ   |
|                |                         | V <sub>R</sub> = 650 V, T <sub>C</sub> = 125°C | -    | 1    | 80   |      |
|                |                         | V <sub>R</sub> = 650 V, T <sub>C</sub> = 175°C | -    | 2    | 160  |      |
| $Q_{C}$        | Total Capacitive Charge | V = 400 V                                      | -    | 51   | -    | nC   |
| С              | Total Capacitance       | V <sub>R</sub> = 1 V, f = 100 kHz              | -    | 866  | -    | pF   |
|                |                         | V <sub>R</sub> = 200 V, f = 100 kHz            | -    | 80   | -    |      |
|                |                         | V <sub>R</sub> = 400 V, f = 100 kHz            | -    | 70   | -    |      |

# TYPICAL CHARACTERISTICS $T_J = 25^{\circ}C$ Unless Otherwise Noted

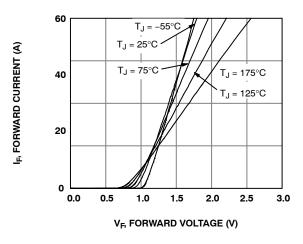


Figure 1. Forward Characteristics

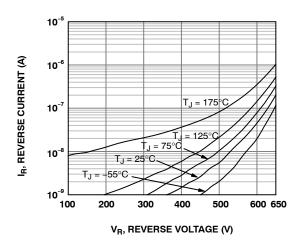


Figure 2. Reverse Characteristics

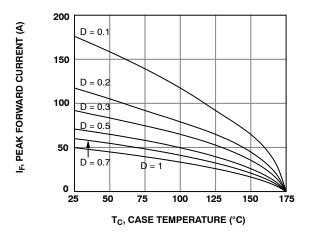


Figure 3. Current Derating

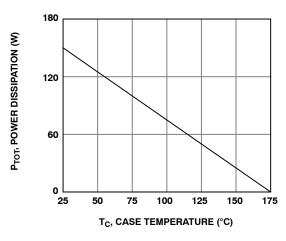


Figure 4. Power Dissipation

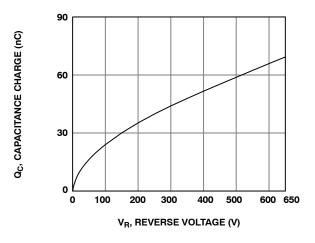


Figure 5. Capacitance Charge vs. Reverse Voltage

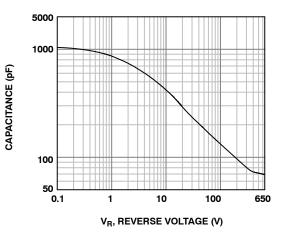


Figure 6. Capacitance vs. Reverse Voltage

## FFSP2065B-F085

# TYPICAL CHARACTERISTICS T<sub>J</sub> = 25°C Unless Otherwise Noted (continued)

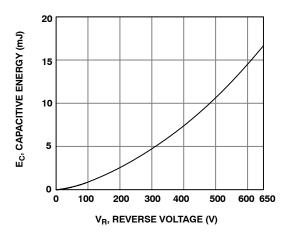


Figure 7. Capacitance Stored Energy

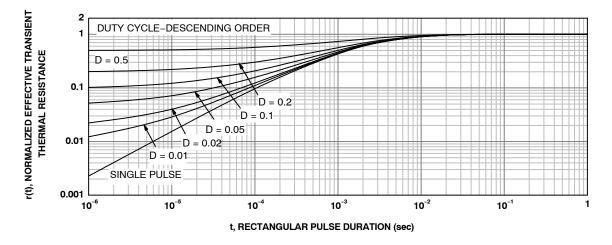


Figure 8. Junction-to-Case Transient Thermal Response Curve

## **TEST CIRCUIT AND WAVEFORMS**

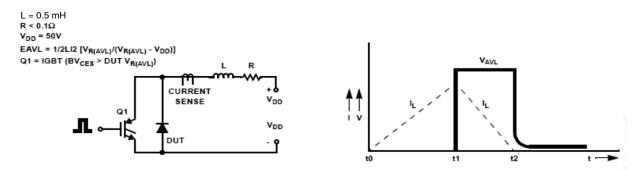
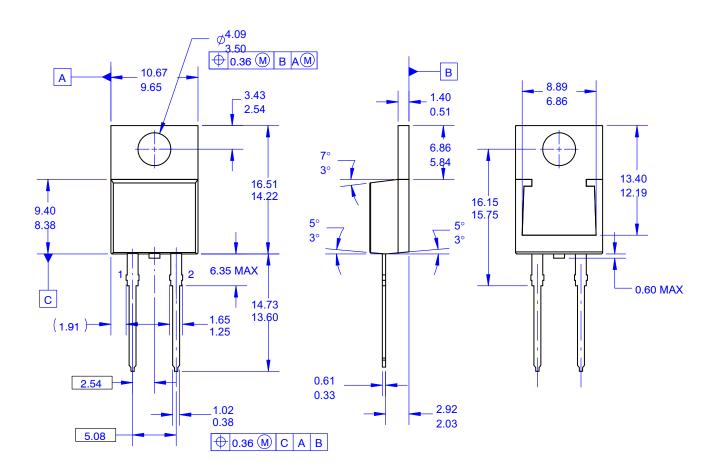


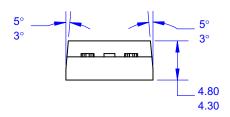
Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



TO-220-2LD CASE 340BB ISSUE O

**DATE 31 AUG 2016** 





#### **NOTES:**

- A. PACKAGE REFERENCE: JEDEC TO220,ISSUE K, VARIATION AC,DATED APRIL 2002.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5–2009.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

| DOCUMENT NUMBER: | 98AON13832G | Electronic versions are uncontrolled except when accessed directly from the Document Repositor<br>Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |             |  |
|------------------|-------------|---|-------------|--|
| DESCRIPTION:     | TO-220-2LD  |   | PAGE 1 OF 1 |  |

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative